

Lista pubblicazioni di Matteo Meneghini

Publication list of Matteo Meneghini

LAVORI SU RIVISTA INTERNAZIONALE

- R1. A.Castaldini, L.Cavallini, L. Rigutti, **M. Meneghini**, S. Levada, G. Meneghesso, E. Zanoni, V. Härle, T. Zahner, U. Zehnder, "Short term instabilities of InGaN GaN light emitting diodes by capacitance–voltage characteristics and junction spectroscopy", *Phys. Stat. Sol. (c)* 2, no. 7, pp. 2862–2865, 2005
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- R4. F. Rossi, M. Pavesi, **M. Meneghini**, G. Salviati, , M. Manfredi, G. Meneghesso, A. Castaldini, A. Cavallini, L. Rigutti, , U. Strass, U. Zehnder, and E. Zanoni, "Influence of short-term low current dc aging on the electrical and optical properties of InGaN blue light-emitting diodes", *J. Appl. Phys.* vol. 99, pp. 053104-1-053104-7, 2006
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- R10. **M. Meneghini**, L.-R. Trevisanello, U. Zehnder, G. Meneghesso, and Enrico Zanoni, "Reversible degradation of ohmic contacts on p-GaN for application in high brightness LEDs", *IEEE Transaction on Electron Devices*, vol. 54, no. 12, pp. 3245 - 3251, 2007
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